

iscN-Channel MOSFET Transistor

IRFBC40AS

• FEATURES

Low drain-source on-resistance:
R_{DS}(ON) = 1.2Ω (MAX)

Enhancement mode:Vth = 2 to 4V (VDS = 10 V, ID=0.25mA)

- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

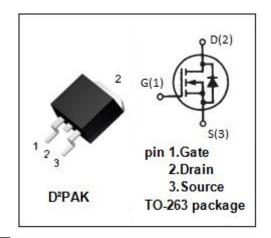
Switching Voltage Regulators



SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	600	V
V _{GS}	Gate-Source Voltage	±30	V
l _D	Drain Current-Continuous	6.2	А
Ірм	Drain Current-Single Pulsed	25	А
P _D	Total Dissipation @T _C =25°C	125	W
Тј	Max. Operating Junction Temperature	-55~150	$^{\circ}\!\mathbb{C}$
T _{stg}	Storage Temperature	-55~150	$^{\circ}\mathbb{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	1	°C/W



B B	K	Q	L
H G		R	V
	m	m	1
DIM	MIN	MAX	1
A	1	0	
В	6.6	6.8	1
C	15.23	15.25	
D	10.15	10 17	
	0.76	0.78	1
F	0.70	0.70	1
F	1.26	1.28	1
F G H	1.26 1.4	1.28 1.6	
F G H J	1.26	0.78 1.28 1.6 1.35	
F G H J	1.26 1.4	0.6	
F G H J K	1.26 1.4 1.33	1.35 0.6 4.8	
F G H J	1.26 1.4 1.33 0.4 4.6 8.69	1.35 0.6 4.8 8.71	
F G H J K L	1.26 1.4 1.33 0.4	1.35 0.6 4.8 8.71	
F G H J K L	1.26 1.4 1.33 0.4 4.6 8.69 5.28	1.35 0.6 4.8 8.71 5.30	
F G H J K L Q R	1.26 1.4 1.33 0.4 4.6 8.69 5.28 1.26	1.35 0.6 4.8 8.71 5.30 1.28	
F G H J K L Q	1.26 1.4 1.33 0.4 4.6 8.69 5.28	1.35 0.6 4.8 8.71 5.30	



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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	600			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = 10V; I _D =0.25mA	2		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =3.7A			1.2	Ω
lgss	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} = 0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =600V; V _{GS} = 0V V _{DS} =480V; V _{GS} = 0V;T _J =125°C			25 250	μА
V _{SDF}	Diode forward voltage	I _{DR} =6.2A, V _{GS} = 0 V			1.5	V

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